Jennifer Wong-Leung

List of Publications by Year
in descending order

171 papers	5,456 citations	101543 36 h-index	88630 70 g-index
174 all docs	174 docs citations	174 times ranked	5435 citing authors

#	Article	IF	Citations
1	Tuning the crystal structure and optical properties of selective area grown InGaAs nanowires. Nano Research, 2022, 15, 3695-3703.	10.4	5
2	Impact of Halide Anions in CsX (Xâ€‰=â€‰I, Br, Cl) on the Microstructure and Photovoltaic Performance of FAPbI₃â€Based Perovskite Solar Cells. Solar Rrl, 2022, 6, .	5.8	4
3	Understanding the role of facets and twin defects in the optical performance of GaAs nanowires for laser applications. Nanoscale Horizons, 2021, 6, 559-567.	8.0	11
4	Unraveling the influence of CsCl/MACl on the formation of nanotwins, stacking faults and cubic supercell structure in FA-based perovskite solar cells. Nano Energy, 2021, 87, 106226.	16.0	27
5	Role of defects and grain boundaries in the thermal response of wafer-scale hBN films. Nanotechnology, 2021, 32, 075702.	2.6	6
6	Engineering IIIâ€“V Semiconductor Nanowires for Device Applications. Advanced Materials, 2020, 32, e1904359.	21.0	43
7	Facet-Related Non-uniform Photoluminescence in Passivated GaAs Nanowires. Frontiers in Chemistry, 2020, 8, 607481.	3.6	2
8	Highly regular rosette-shaped cathodoluminescence in GaN self-assembled nanodisks and nanorods. Nano Research, 2020, 13, 2500-2505.	10.4	6
9	Insights into Twinning Formation in Cubic and Tetragonal Multi-cation Mixed-Halide Perovskite. , 2020, 2, 415-424.		17
10	Cathodoluminescence visualisation of local thickness variations of GaAs/AlGaAs quantum-well tubes on nanowires. Nanotechnology, 2020, 31, 424001.	2.6	4
11	Highly uniform InGaAs/InP quantum well nanowire array-based light emitting diodes. Nano Energy, 2020, 71, 104576.	16.0	23
12	Improving the Morphology and Crystal Quality of AlN Grown on Two-Dimensional hBN. Crystal Growth and Design, 2020, 20, 1811-1819.	3.0	7
13	Exploring the band structure of Wurtzite InAs nanowires using photocurrent spectroscopy. Nano Research, 2020, 13, 1586-1591.	10.4	7
14	High Efficiency Perovskiteâ€Silicon Tandem Solar Cells: Effect of Surface Coating versus Bulk Incorporation of 2D Perovskite. Advanced Energy Materials, 2020, 10, 1903553.	19.5	110
15	Understanding the Chemical and Structural Properties of Multiple-Cation Mixed Halide Perovskite. Journal of Physical Chemistry C, 2019, 123, 26718-26726.	3.1	14
16	InGaAsP as a Promising Narrow Band Gap Semiconductor for Photoelectrochemical Water Splitting. ACS Applied Materials & Interfaces, 2019, 11, 25236-25242.	8.0	21
17	Multiwavelength Single Nanowire InGaAs/InP Quantum Well Light-Emitting Diodes. Nano Letters, 2019, 19, 3821-3829.	9.1	32
18	Ultrathin Ta₂O₅ electron-selective contacts for high efficiency InP solar cells. Nanoscale, 2019, 11, 7497-7505.	5.6	38

#	Article	IF	Citations
19	Large area hexagonal boron nitride coatings for SERS applications with silver nanoparticles. , 2019, , .		0
20	Engineering IIIâ€“V Nanowires for Optoelectronics: From Visible to Terahertz. , 2019, , .		0
21	Direct Observation of the Impurity Gettering Layers in Polysilicon-Based Passivating Contacts for Silicon Solar Cells. ACS Applied Energy Materials, 2018, 1, 2275-2282.	5.1	22
22	CdS/TiO₂ photoanodes via solution ion transfer method for highly efficient solar hydrogen generation. Nano Futures, 2018, 2, 015004.	2.2	19
23	Impurity Gettering by Diffusion-doped Polysilicon Passivating Contacts for Silicon Solar Cells. , 2018, , .		2
24	Radial Growth Evolution of InGaAs/InP Multi-Quantum-Well Nanowires Grown by Selective-Area Metal Organic Vapor-Phase Epitaxy. ACS Nano, 2018, 12, 10374-10382.	14.6	26
25	The effect of nitridation on the polarity and optical properties of GaN self-assembled nanorods. Nanoscale, 2018, 10, 11205-11210.	5.6	9
26	Perovskite Photovoltaic Integrated CdS/TiO₂ Photoanode for Unbiased Photoelectrochemical Hydrogen Generation. ACS Applied Materials & Interfaces, 2018, 10, 23766-23773.	8.0	38
27	Flow modulation epitaxy of hexagonal boron nitride. 2D Materials, 2018, 5, 045018.	4.4	57
28	Engineering III-V nanowires for optoelectronics: from epitaxy to terahertz photonics. , 2018, , .		0
29	Comparison of the structural properties of Zn-face and O-face single crystal homoepitaxial ZnO epilayers grown by RF-magnetron sputtering. Journal of Applied Physics, 2017, 121, .	2.5	5
30	Influence of Interface Morphology on Hysteresis in Vaporâ€Deposited Perovskite Solar Cells. Advanced Electronic Materials, 2017, 3, 1600470.	5.1	63
31	Semiconductor nanowires in terahertz photonics: From spectroscopy to ultrafast nanowire-based devices. , 2017, , .		0
32	Engineering the Photoresponse of InAs Nanowires. ACS Applied Materials & Interfaces, 2017, 9, 43993-44000.	8.0	49
33	Critical Temperature for the Conversion from Wurtzite to Zincblende of the Optical Emission of InAs Nanowires. Journal of Physical Chemistry C, 2017, 121, 16650-16656.	3.1	2
34	Zn precipitation and Li depletion in Zn implanted ZnO. Applied Physics Letters, 2016, 109, 022102.	3.3	3
35	Suppression of ion-implantation induced porosity in germanium by a silicon dioxide capping layer. Applied Physics Letters, 2016, 109, .	3.3	16
36	Simultaneous Selective-Area and Vaporâ€“Liquidâ€“Solid Growth of InP Nanowire Arrays. Nano Letters, 2016, 16, 4361-4367.	9.1	57

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37	Photoluminescence Excitation Spectroscopy of Diffused Layers on Crystalline Silicon Wafers. IEEE Journal of Photovoltaics, 2016, 6, 746-753.	2.5	6
38	Tunable Polarity in a IIIâ€“V Nanowire by Droplet Wetting and Surface Energy Engineering. Advanced Materials, 2015, 27, 6096-6103.	21.0	69
39	Controlling the morphology, composition and crystal structure in gold-seeded GaAs_{1âˆ’x}Sb_xnanowires. Nanoscale, 2015, 7, 4995-5003.	5.6	56
40	InxGa1âˆ’xAs nanowires with uniform composition, pure wurtzite crystal phase and taper-free morphology. Nanotechnology, 2015, 26, 205604.	2.6	36
41	Equilibrium shape of nano-cavities in H implanted ZnO. Applied Physics Letters, 2015, 106, .	3.3	6
42	InP-based radial heterostructures grown on [100] nanowires. , 2014, , .		0
43	Sidewall evolution in VLS grown GaAs nanowires. , 2014, , .		0
44	How InAs crystal phase affects the electrical performance of InAs nanowire FETs. , 2014, , .		2
45	Effects of high temperature annealing on defects and luminescence properties in H implanted ZnO. Journal Physics D: Applied Physics, 2014, 47, 342001.	2.8	8
46	Understanding the True Shape of Au-Catalyzed GaAs Nanowires. Nano Letters, 2014, 14, 5865-5872.	9.1	52
47	Selective-Area Epitaxy of Pure Wurtzite InP Nanowires: High Quantum Efficiency and Room-Temperature Lasing. Nano Letters, 2014, 14, 5206-5211.	9.1	198
48	Nanowires Grown on InP (100): Growth Directions, Facets, Crystal Structures, and Relative Yield Control. ACS Nano, 2014, 8, 6945-6954.	14.6	51
49	Polarity-Driven 3-Fold Symmetry of GaAs/AlGaAs Core Multishell Nanowires. Nano Letters, 2013, 13, 3742-3748.	9.1	80
50	Twinning Superlattice Formation in GaAs Nanowires. ACS Nano, 2013, 7, 8105-8114.	14.6	77
51	Electron-pinned defect-dipoles for high-performance colossal permittivity materials. Nature Materials, 2013, 12, 821-826.	27.5	784
52	Enhanced Minority Carrier Lifetimes in GaAs/AlGaAs Coreâ€“Shell Nanowires through Shell Growth Optimization. Nano Letters, 2013, 13, 5135-5140.	9.1	97
53	Direct Observation of Charge-Carrier Heating at WZâ€“ZB InP Nanowire Heterojunctions. Nano Letters, 2013, 13, 4280-4287.	9.1	31
54	Measuring the electrical properties of semiconductor nanowires using terahertz conductivity spectroscopy. Proceedings of SPIE, 2013, , .	0.8	0

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55	High vertical yield InP nanowire growth on Si(111) using a thin buffer layer. Nanotechnology, 2013, 24, 465602.	2.6	21
56	Defect formation and thermal stability of H in high dose H implanted ZnO. Journal of Applied Physics, 2013, 114, 083111.	2.5	19
57	Probing the critical electronic properties of III–V nanowires using optical pump-terahertz probe spectroscopy. , 2013, , .		0
58	High performance GaAs/AlGaAs radial heterostructure nanowires grown by MOCVD. , 2013, , .		0
59	Compound semiconductor nanowires for optoelectronic devices. , 2013, , .		0
60	Electronic comparison of InAs wurtzite and zincblende phases using nanowire transistors. Physica Status Solidi - Rapid Research Letters, 2013, 7, 911-914.	2.4	15
61	Anomalous Diffusion of Intrinsic Defects in K+ Implanted ZnO using Li as Tracer. Materials Research Society Symposia Proceedings, 2012, 1394, 75.	0.1	2
62	Direct correlation of R-line luminescence with rod-like defect evolution in ion-implanted and annealed silicon. MRS Communications, 2012, 2, 101-105.	1.8	2
63	Acceptor-like deep level defects in ion-implanted ZnO. Applied Physics Letters, 2012, 100, 212106.	3.3	15
64	Long minority carrier lifetime in Au-catalyzed GaAs/AlxGa1â^’xAs core-shell nanowires. Applied Physics Letters, 2012, 101, .	3.3	80
65	Polarization Tunable, Multicolor Emission from Coreâ€“Shell Photonic IIIâ€“V Semiconductor Nanowires. Nano Letters, 2012, 12, 6428-6431.	9.1	27
66	InP nanowires grown by SA-MOVPE. , 2012, , .		1
67	Structural and optical properties of H implanted ZnO. , 2012, , .		0
68	Improvement of minority carrier lifetime in GaAs/Al<inf>x</inf>Ga<inf>1−x</inf>As core-shell nanowires. , 2012, , .		0
69	Growth and characterization of GaAs<inf>1−x</inf>Sb<inf>x</inf> nanowires. , 2012, , .		0
70	Influence of growth temperature and V/III ratio on Au-assisted In<inf>x</inf>Ga<inf>1−x</inf>As nanowires. , 2012, , .		0
71	Ultralow Surface Recombination Velocity in InP Nanowires Probed by Terahertz Spectroscopy. Nano Letters, 2012, 12, 5325-5330.	9.1	158
72	Anderson-like localization in ultrathin nanocomposite alloy films on polymeric substrates. Scripta Materialia, 2012, 67, 866-869.	5.2	2

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73	Dopant effects on the photoluminescence of interstitial-related centers in ion implanted silicon. Journal of Applied Physics, 2012, 111, 094910.	2.5	3
74	Ion implantation induced defects in ZnO. Physica B: Condensed Matter, 2012, 407, 1481-1484.	2.7	11
75	Selective Intermixing of InGaAs/GaAs Quantum Dot Infrared Photodetectors. IEEE Journal of Quantum Electronics, 2011, 47, 577-590.	1.9	7
76	Tailoring GaAs, InAs, and InGaAs Nanowires for Optoelectronic Device Applications. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 766-778.	2.9	40
77	Growth of Straight InAs-on-GaAs Nanowire Heterostructures. Nano Letters, 2011, 11, 3899-3905.	9.1	44
78	Effect of boron on formation of interstitialâ€related luminescence centres in ion implanted silicon. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 620-623.	1.8	2
79	Growth and Characterization of Self-Assembled InAs/InP Quantum Dot Structures. Journal of Nanoscience and Nanotechnology, 2010, 10, 1525-1536.	0.9	7
80	Spectral tuning of InGaAs/GaAs quantum dot infrared photodetectors using selective-area intermixing. , 2010, , .		1
81	Effect of boron on interstitial-related luminescence centers in silicon. Applied Physics Letters, 2010, 96, 051906.	3.3	13
82	Phase Perfection in Zinc Blende and Wurtzite IIIâˆ’V Nanowires Using Basic Growth Parameters. Nano Letters, 2010, 10, 908-915.	9.1	443
83	Comparison between implanted boron and phosphorus in silicon wafers.. , 2010, , .		1
84	Achieving a narrow size distribution of Au particles at a precise depth in SiO₂by segregation of Au precipitates. Nanotechnology, 2009, 20, 185603.	2.6	1
85	Self-assembled Au nanoparticles in SiO2 by ion implantation and wet oxidation. Journal of Applied Physics, 2009, 106, 103526.	2.5	6
86	Voids and Nanocavities in Silicon. Topics in Applied Physics, 2009, , 113-146.	0.8	3
87	Ion implantation in 4Hâ€“SiC. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 1367-1372.	1.4	15
88	Tuning the bandgap of InAs quantum dots by selective-area MOCVD. Journal Physics D: Applied Physics, 2008, 41, 085104.	2.8	5
89	Electric field assisted annealing and formation of prominent deep-level defect in ion-implanted n-type 4H-SiC. Applied Physics Letters, 2008, 92, .	3.3	15
90	Point defect engineered Si sub-bandgap light-emitting diodes. Proceedings of SPIE, 2007, , .	0.8	1

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91	The formation, migration, agglomeration and annealing of vacancy-type defects in self-implanted Si. Journal of Materials Science: Materials in Electronics, 2007, 18, 695-700.	2.2	9
92	Ion Implantation Processing and Related Effects in SiC. Materials Science Forum, 2006, 527-529, 781-786.	0.3	11
93	Photoluminescence response of ion-implanted silicon. Applied Physics Letters, 2006, 89, 181917.	3.3	13
94	The role of arsine in the self-assembled growth of InAsâˆ•GaAs quantum dots by metal organic chemical vapor deposition. Journal of Applied Physics, 2006, 99, 044908.	2.5	13
95	Formation of precipitates in heavily boron doped 4H-SiC. Applied Surface Science, 2006, 252, 5316-5320.	6.1	12
96	A transmission electron microscopy study of defects formed through the capping layer of self-assembled InAsâˆ•GaAs quantum dot samples. Journal of Applied Physics, 2006, 99, 113503.	2.5	28
97	Identification by photoluminescence and positron annihilation of vacancy and interstitial intrinsic defects in ion-implanted silicon. Journal of Applied Physics, 2006, 100, 073501.	2.5	6
98	Effects of rapid thermal annealing on device characteristics of InGaAsâˆ•GaAs quantum dot infrared photodetectors. Journal of Applied Physics, 2006, 99, 114517.	2.5	45
99	InAs quantum dots grown on InGaAs buffer layers by metalâ€“organic chemical vapor deposition. Journal of Crystal Growth, 2005, 281, 290-296.	1.5	6
100	Ion irradiation-induced disordering of semiconductors: defect structures and applications. Philosophical Magazine, 2005, 85, 677-687.	1.6	6
101	Fluence, flux, and implantation temperature dependence of ion-implantation-induced defect production in 4Hâ€“SiC. Journal of Applied Physics, 2005, 97, 033513.	2.5	26
102	Ion-implantation-induced extended defect formation in (0001) and(112Â¯0)4Hâˆ’SiC. Physical Review B, 2005, 71, .	3.2	31
103	Compound semiconductor optoelectronics research at the Australian National University. , 2005, , .		0
104	Ion implantation effects in silicon with high carbon content characterised by photoluminescence. Physica B: Condensed Matter, 2003, 340-342, 714-718.	2.7	1
105	Study of defects in ion-implanted silicon using photoluminescence and positron annihilation. Physica B: Condensed Matter, 2003, 340-342, 738-742.	2.7	7
106	A comparison of extended defect formation induced by ion implantation in (0001) and (112Ì„0) 4H-SiC. Physica B: Condensed Matter, 2003, 340-342, 132-136.	2.7	2
107	Solubility limits of dopants in 4Hâ€“SiC. Applied Surface Science, 2003, 203-204, 427-432.	6.1	18
108	Low loss, thin p-clad 980-nm InGaAs semiconductor laser diodes with an asymmetric structure design. IEEE Journal of Quantum Electronics, 2003, 39, 625-633.	1.9	33

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109	Effect of crystal orientation on the implant profile of 60 keV Al into 4H-SiC crystals. Journal of Applied Physics, 2003, 93, 8914-8917.	2.5	42
110	Influence of rapid thermal annealing on a 30 stack InAs/GaAs quantum dot infrared photodetector. Journal of Applied Physics, 2003, 94, 5283.	2.5	37
111	Vacancy and interstitial depth profiles in ion-implanted silicon. Journal of Applied Physics, 2003, 93, 871-877.	2.5	22
112	Dynamic annealing in ion implanted SiC: Flux versus temperature dependence. Journal of Applied Physics, 2003, 94, 7112-7115.	2.5	44
113	Identification of hydrogen related defects in proton implanted float-zone silicon. EPJ Applied Physics, 2003, 23, 5-9.	0.7	14
114	Response to â€œComment on â€˜Separation of vacancy and interstitial depth profiles in ion-implanted silicon: Experimental observationâ€™â€Šâ€•[Appl. Phys. Lett. 80, 1492 (2002)]. Applied Physics Letters, 2002, 80, 1494-1495.	3.3	1
115	Indentation-induced damage in GaN epilayers. Applied Physics Letters, 2002, 80, 383-385.	3.3	107
116	Ion mass effect on vacancy-related deep levels in Si induced by ion implantation. Physical Review B, 2002, 65, .	3.2	40
117	Spherical indentation of compound semiconductors. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 2002, 82, 1931-1939.	0.6	28
118	Suppression of interdiffusion in GaAs/AlGaAs quantum-well structure capped with dielectric films by deposition of gallium oxide. Journal of Applied Physics, 2002, 92, 3579-3583.	2.5	35
119	Nanoindentation-induced deformation of Ge. Applied Physics Letters, 2002, 80, 2651-2653.	3.3	70
120	Separation of vacancy and interstitial depth profiles in proton- and boron-implanted silicon. Nuclear Instruments & Methods in Physics Research B, 2002, 186, 334-338.	1.4	5
121	Spherical indentation of compound semiconductors. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 2002, 82, 1931-1939.	0.6	7
122	Solubility limit and precipitate formation in Al-doped 4H-SiC epitaxial material. Applied Physics Letters, 2001, 79, 2016-2018.	3.3	43
123	Mechanical deformation of InP and GaAs by spherical indentation. Applied Physics Letters, 2001, 78, 3235-3237.	3.3	94
124	Capture cross sections of the acceptor level of ironâ€“boron pairs in p-type silicon by injection-level dependent lifetime measurements. Journal of Applied Physics, 2001, 89, 7932-7939.	2.5	75
125	Mechanical deformation in silicon by micro-indentation. Journal of Materials Research, 2001, 16, 1500-1507.	2.6	234
126	Direct observation of voids in the vacancy excess region of ion bombarded silicon. Applied Physics Letters, 2001, 78, 2867-2869.	3.3	28

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127	Efficiency of dislocations and cavities for gettering of Cu and Fe in silicon. Nuclear Instruments & Methods in Physics Research B, 2001, 175-177, 154-158.	1.4	2
128	The crystallisation of deep amorphous wells in silicon produced by ion implantation. Nuclear Instruments & Methods in Physics Research B, 2001, 175-177, 164-168.	1.4	6
129	Interaction of defects and metals with nanocavities in silicon. Nuclear Instruments & Methods in Physics Research B, 2001, 178, 33-43.	1.4	29
130	Defect formation due to the crystallization of deep amorphous volumes formed in silicon by mega electron volt (MeV) ion implantation. Journal of Materials Research, 2001, 16, 3229-3237.	2.6	5
131	Selectivity of nanocavities and dislocations for gettering of Cu and Fe in silicon. Applied Physics Letters, 2001, 78, 2682-2684.	3.3	12
132	Separation of vacancy and interstitial depth profiles in ion-implanted silicon: Experimental observation. Applied Physics Letters, 2001, 78, 3442-3444.	3.3	32
133	Effect of implant temperature on secondary defects created by MeV Sn implantation in silicon. Journal of Applied Physics, 2001, 89, 2556-2559.	2.5	16
134	Interactions of Point Defects and Impurities With Open Volume Defects in Silicon. Materials Research Society Symposia Proceedings, 2000, 647, 1.	0.1	0
135	Mechanical Deformation of Crystalline Silicon During Nanoindentation. Materials Research Society Symposia Proceedings, 2000, 649, 8101.	0.1	4
136	Transmission electron microscopy characterization of secondary defects created by MeV Si, Ge, and Sn implantation in silicon. Journal of Applied Physics, 2000, 88, 1312-1318.	2.5	10
137	Effect of Implant Temperature on Extended Defects Craeted by Ion Implantation in Silicon. Defect and Diffusion Forum, 2000, 183-185, 163-170.	0.4	1
138	Transmission electron microscopy observation of deformation microstructure under spherical indentation in silicon. Applied Physics Letters, 2000, 77, 3749-3751.	3.3	210
139	Effect of ion mass on the evolution of extended defects during annealing of MeV ion-implanted p-type Si. Applied Physics Letters, 1999, 74, 1141-1143.	3.3	19
140	Diffusion and transient trapping of metals in silicon. Physical Review B, 1999, 59, 7990-7998.	3.2	31
141	Ultra-micro-indentation of silicon and compound semiconductors with spherical indenters. Journal of Materials Research, 1999, 14, 2338-2343.	2.6	94
142	The role of Fe on the crystallisation of Î±-Si3N4 from amorphous Siâ€“N formed by ion implantation. Nuclear Instruments & Methods in Physics Research B, 1999, 148, 534-539.	1.4	6
143	The role of oxygen on the stability of gettering of metals to cavities in silicon. Applied Physics Letters, 1999, 75, 2424-2426.	3.3	25
144	Analysis of semiconductors by ion channelling: Applications and pitfalls. Nuclear Instruments & Methods in Physics Research B, 1998, 136-138, 453-459.	1.4	7

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145	The precipitation of Fe at the Siâ€"SiO2 interface. Journal of Applied Physics, 1998, 83, 580-584.	2.5	42
146	The influence of cavities and point defects on boron diffusion in silicon. Applied Physics Letters, 1998, 72, 2418-2420.	3.3	15
147	Microstructural difference between platinum and silver trapped in hydrogen induced cavities in silicon. Applied Physics Letters, 1998, 72, 2713-2715.	3.3	13
148	Efficient gettering of low concentrations of copper contamination to hydrogen induced nanocavities in silicon. Applied Physics Letters, 1998, 73, 2639-2641.	3.3	14
149	Electrical characterization of the threshold fluence for extended defect formation in p-type silicon implanted with MeV Si ions. Applied Physics Letters, 1998, 72, 3044-3046.	3.3	21
150	Characterisation of the Subthreshold Damage in MeV Ion Implanted p Si. Materials Research Society Symposia Proceedings, 1998, 510, 411.	0.1	0
151	The Influence of Cavities and Point Defects on Cu Gettering and B'Diffusion in Si. Materials Research Society Symposia Proceedings, 1997, 469, 457.	0.1	2
152	Non-Equilibrium Formation Of Silicon Nitride During Both Ball Milling And Ion Bombardment. Materials Research Society Symposia Proceedings, 1997, 481, 439.	0.1	2
153	Gettering of platinum and silver to cavities formed by hydrogen implantation in silicon. Nuclear Instruments & Methods in Physics Research B, 1997, 127-128, 297-300.	1.4	21
154	Rutherford backscattering and channeling study of Au trapped at cavities in silicon. Nuclear Instruments & Methods in Physics Research B, 1996, 118, 34-38.	1.4	5
155	Defect Evolution in Hydrogen Implanted Silicon. , 1996, , 832-836.		4
156	Transient Diffusion and Gettering of Au and Cu to Cavities in Si. Materials Research Society Symposia Proceedings, 1995, 378, 273.	0.1	1
157	Diffusion and trapping of Au to cavities induced by H-implantation in Si. Nuclear Instruments & Methods in Physics Research B, 1995, 106, 424-428.	1.4	22
158	Proximity gettering of Au to ion beam induced defects in silicon. Nuclear Instruments & Methods in Physics Research B, 1995, 96, 253-256.	1.4	33
159	Gettering of copper to hydrogenâ€induced cavities in silicon. Applied Physics Letters, 1995, 66, 1231-1233.	3.3	123
160	Gettering of nickel to cavities in silicon introduced by hydrogen implantation. Applied Physics Letters, 1995, 66, 1889-1891.	3.3	66
161	Gettering of Au to dislocations and cavities in silicon. Applied Physics Letters, 1995, 67, 416-418.	3.3	85
162	Defect Trapping and Precipitation Processes During Annealing of Cu and Au Implanted Si. Materials Research Society Symposia Proceedings, 1994, 354, 255.	0.1	4

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163	Microstructure of Irradiated Silicon. Materials Research Society Symposia Proceedings, 1994, 373, 543.	0.1	3
164	Gettering of metals to nanocavities in silicon. , 0, , .		1
165	Strain relaxation in rapid thermally annealed InAs/GaAs quantum dot infrared photodetectors. , 0, , .		0
166	Asymmetric design of semiconductor laser diodes: thin p-clad and low divergence InGaAs/AlGaAs/GaAs devices. , 0, , .		1
167	Spatial selectivity of impurity free vacancy disordering using different dielectric layers for photonic/optoelectronic integrated circuits. , 0, , .		0
168	Growth and Characterisation of InAs/GaAs Quantum Dots Grown by MOCVD. , 0, , .		6
169	Proton Irradiation Induced Intermixing in In_xGa_1-xAs/InP Quantum Wells. , 0, , .		0
170	Controlled nucleation of InAs/GaAs and InGaAs/GaAs quantum dots for optoelectronic device integration. , 0, , .		0
171	Mn Implantation for New Applications of 4H-SiC. Materials Science Forum, 0, 717-720, 221-224.	0.3	1